

## N-Channel 1200-V (D-S) MOSFET

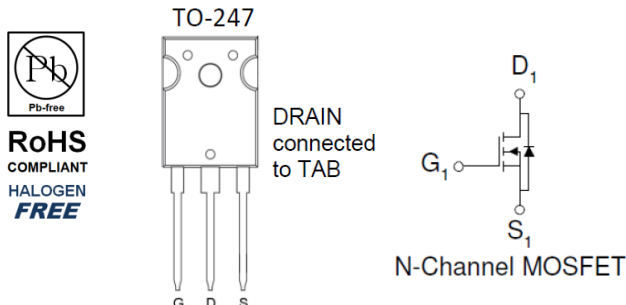
### Key Features:

- Low  $r_{DS(on)}$  trench technology
- Low thermal impedance
- Fast switching speed

### Typical Applications:

- White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY		
$V_{DS}$ (V)	$r_{DS(on)}$ (m $\Omega$ )	$I_D$ (A)
1200	80 @ $V_{GS} = 20V$	8 <sup>a</sup>
	90 @ $V_{GS} = 18V$	



### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter	Symbol	Limit	Units
Drain-Source Voltage	$V_{DS}$	1200	V
Gate-Source Voltage	$V_{GS}$	$\pm 25$	
Continuous Drain Current <sup>a</sup>	$I_D$	8	A
Pulsed Drain Current <sup>b</sup>			
Continuous Source Current (Diode Conduction) <sup>a</sup>	$I_S$	8	A
Power Dissipation <sup>a</sup>	$P_D$	500	W
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to 175	$^\circ\text{C}$

### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Maximum	Units
Maximum Junction-to-Ambient <sup>c</sup>	$R_{\theta JA}$	40	$^\circ\text{C/W}$
Maximum Junction-to-Case	$R_{\theta JC}$	0.29	

### Notes

- Package Limited
- Pulse width limited by maximum junction temperature
- Surface Mounted on 1" x 1" FR4 Board.

## Electrical Characteristics

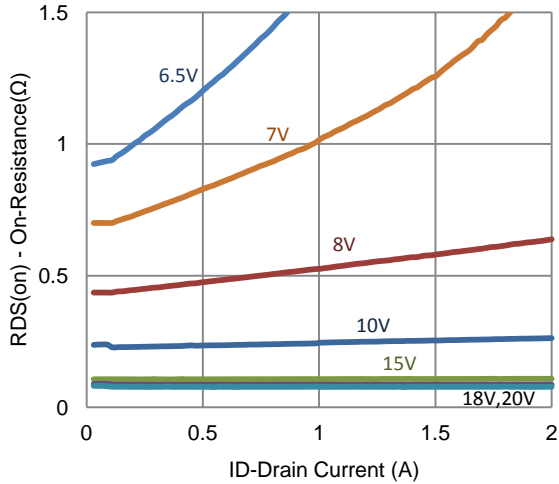
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
<b>Static</b>						
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 10 \text{ mA}$	2			V
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 25 \text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 960 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA
		$V_{DS} = 960 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 55^\circ\text{C}$			10	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	10			A
Drain-Source On-Resistance <sup>a</sup>	$r_{DS(on)}$	$V_{GS} = 20 \text{ V}, I_D = 2 \text{ A}$			80	mΩ
		$V_{GS} = 18 \text{ V}, I_D = 1.8 \text{ A}$			90	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 50 \text{ V}, I_D = 2 \text{ A}$		4		S
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_S = 4 \text{ A}, V_{GS} = 0 \text{ V}$		2.86		V
<b>Dynamic <sup>b</sup></b>						
Total Gate Charge	$Q_g$	$V_{DS} = 100 \text{ V}, V_{GS} = 6 \text{ V},$ $I_D = 0.5 \text{ A}$		16		nC
Gate-Source Charge	$Q_{gs}$			9.8		
Gate-Drain Charge	$Q_{gd}$			4.4		
Turn-On Delay Time	$t_{d(on)}$	$V_{DS} = 100 \text{ V}, R_L = 200 \Omega,$ $I_D = 0.5 \text{ A},$ $V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		18		ns
Rise Time	$t_r$			10		
Turn-Off Delay Time	$t_{d(off)}$			46		
Fall Time	$t_f$			82		
Input Capacitance	$C_{iss}$	$V_{DS} = 50 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		1135		pF
Output Capacitance	$C_{oss}$			217		
Reverse Transfer Capacitance	$C_{rss}$			15		

## Notes

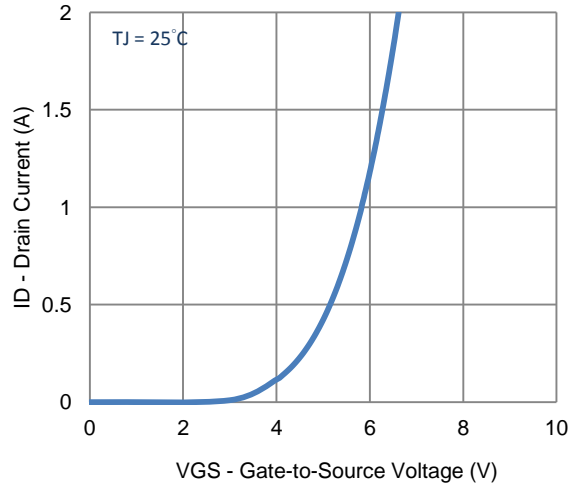
- Pulse test:  $PW \leq 300\mu\text{s}$  duty cycle  $\leq 2\%$ .
- Guaranteed by design, not subject to production testing.

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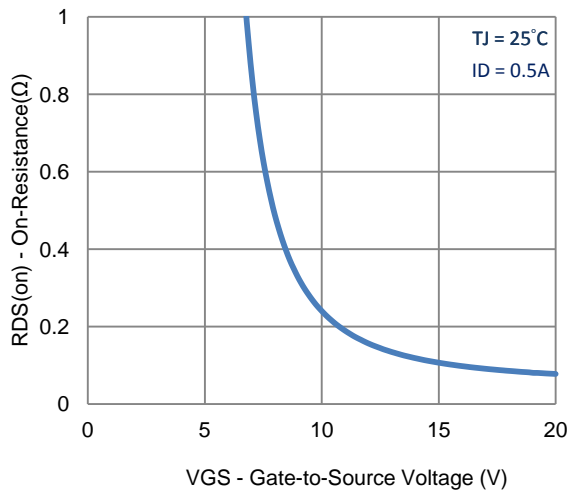
Typical Electrical Characteristics



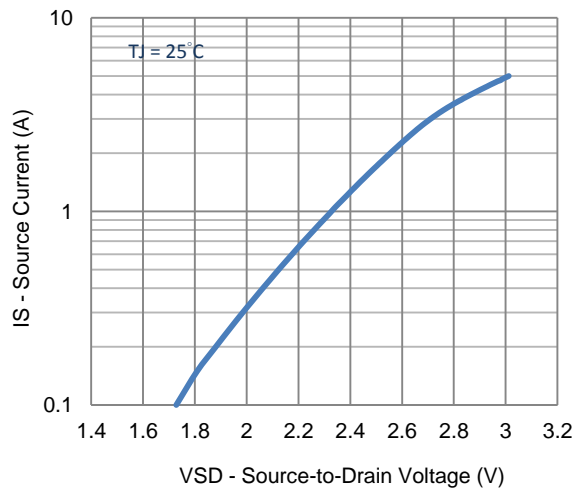
1. On-Resistance vs. Drain Current



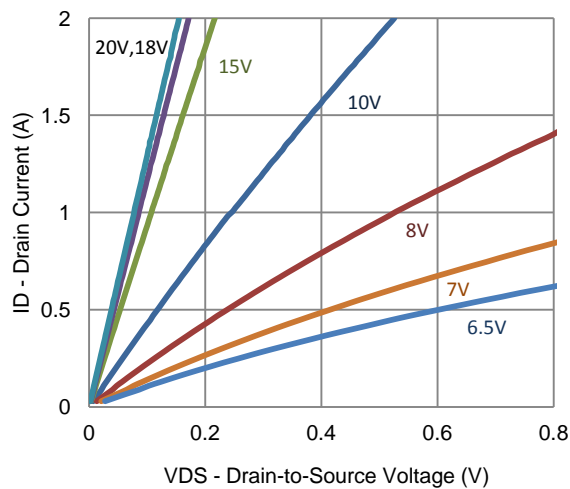
2. Transfer Characteristics



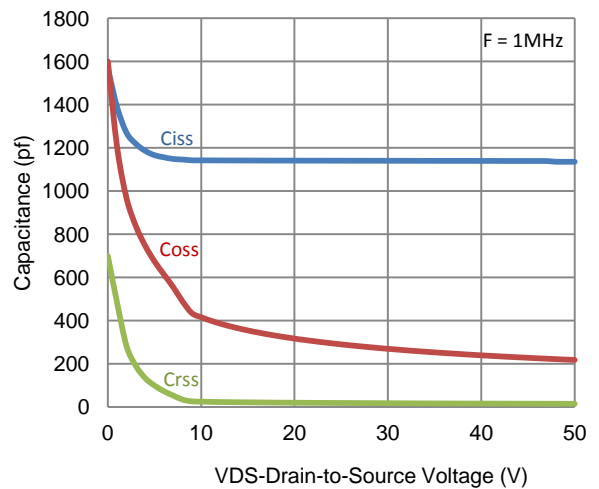
3. On-Resistance vs. Gate-to-Source Voltage



4. Drain-to-Source Forward Voltage

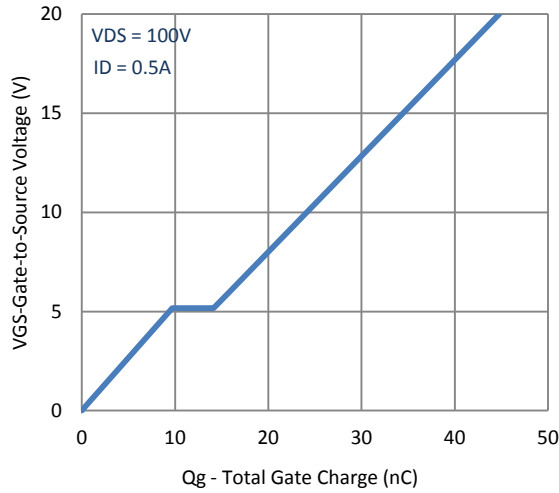


5. Output Characteristics

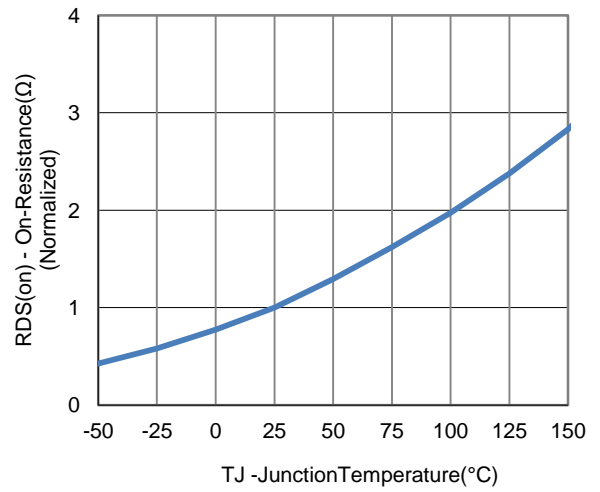


6. Capacitance

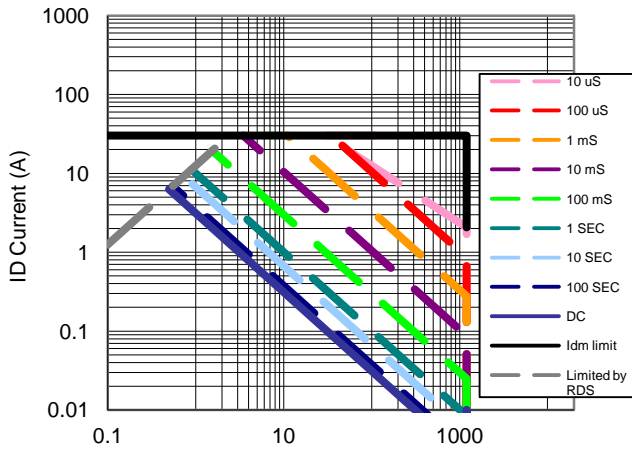
Typical Electrical Characteristics



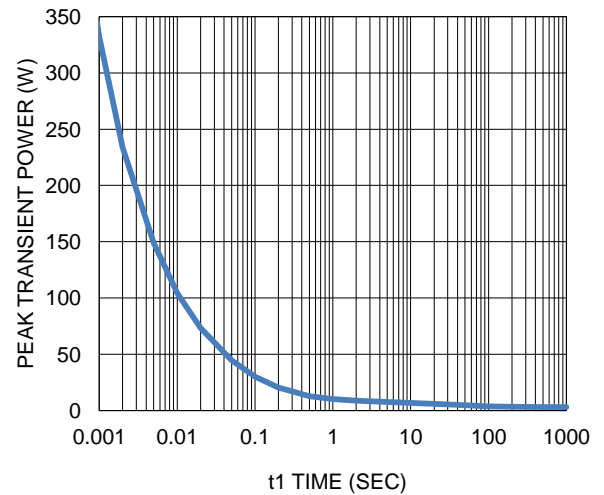
7. Gate Charge



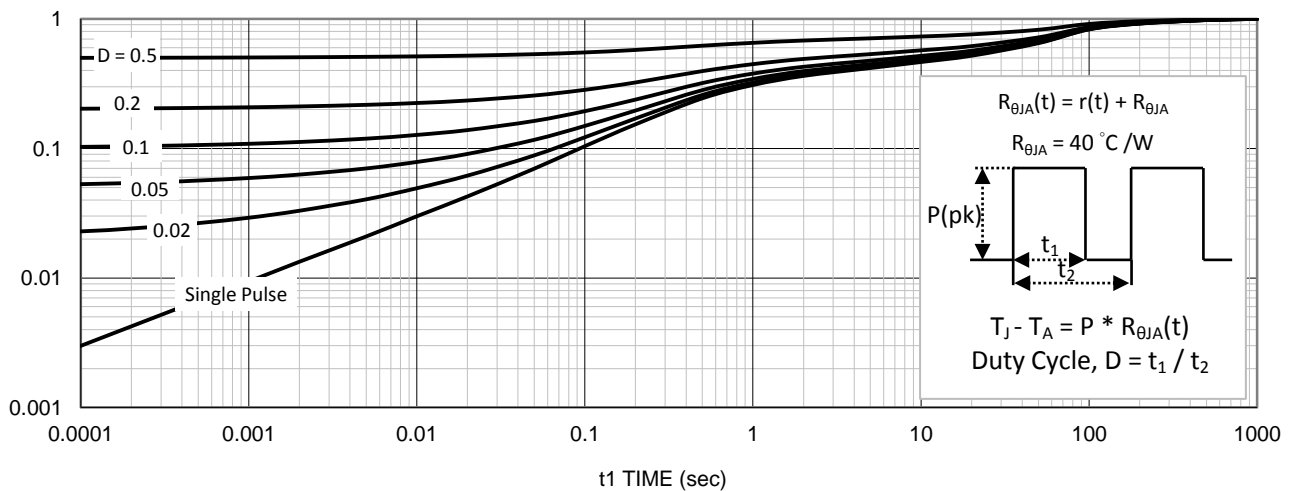
8. Normalized On-Resistance Vs Junction Temperature



9. Safe Operating Area

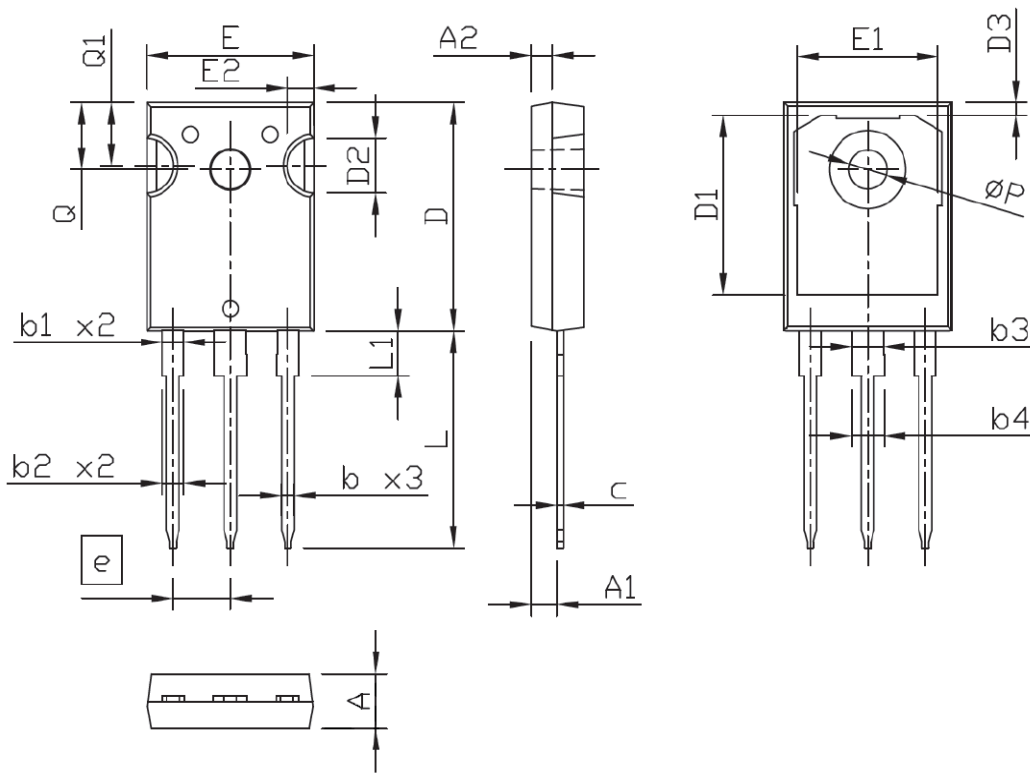


10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

Package Information



SYMBOLS	DIMENSIONS IN MILLIMETERS		
	MIN	NOM	MAX
A	4.90	5.00	5.10
A1	2.32	2.42	2.52
A2	1.90	2.00	2.10
b	1.17	1.22	1.27
b1	1.97	2.02	2.07
b2	2.00	2.10	2.20
b3	2.97	3.02	3.07
b4	3.00	3.10	3.20
c	0.59	0.62	0.66
D	20.90	21.00	21.10
D1	16.25	16.55	16.85
D2	5.00 TYP		
D3	1.05	1.20	1.35
e	5.44 BSC		
E	15.70	15.80	15.90
E1	13.06	13.26	13.46
E2	2.50 TYP		
L	19.72	19.92	20.12
L1	---	---	4.30
Q	6.15 BSC		
Q1	5.60	5.80	6.00
øP	3.55	3.60	3.65